

20W BRIDGE AMPLIFIER FOR CAR RADIO

DESCRIPTION

The TDA2005 is class B dual audio power amplifier, have designed for car radio application.

FEATURES

High output power:

 P_{OUT} =10+10W@R_L=2 Ω , THD=10% P_{OUT} =20W@R_L=4 Ω , THD=1%

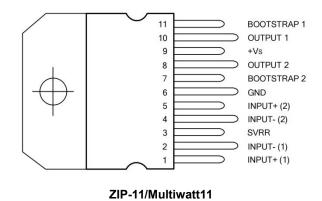


ORDERING INFORMATION

DEVICE	Package Type	MARKING	Packing	Packing Qty
TDA2005R	ZIP-11/Multiwatt11	TDA2005	TUBE	500pcs/box



PIN CONFIGURATION



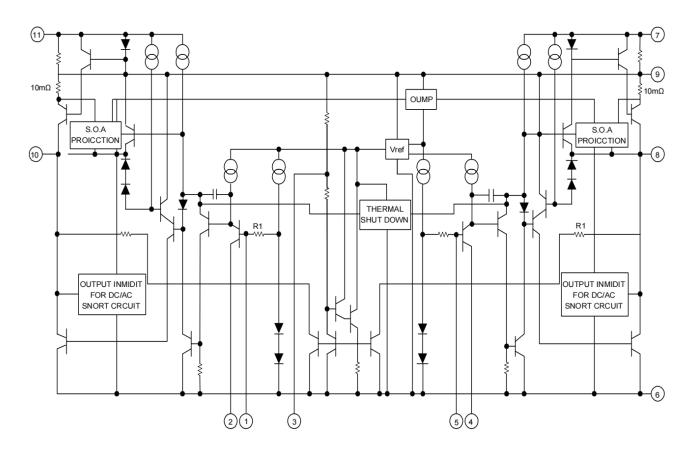
*TAB CONNECTED TO PIN 6

PIN DESCRIPTION

PIN NO. ZIP-11/Multiwatt11	PIN NAME
1	INPUT+ (1)
2	INPUT- (1)
3	SVRR
4	INPUT- (2)
5	INPUT+ (2)
6	GND
7	BOOTSTRAP 2
8	OUTPUT 2
9	+VS
10	OUTPUT 1
11	BOOTSTRAP 1



BLOCK DIAGRAM





ABSOLUTE MAXIMUM RATINGS

PARAMET	ER	SYMBOL	RATINGS	UNIT
Operating Supply Voltage		Vss	18	V
DC Supply Voltage		Vss	28	V
Peak Supply Voltage (for 50ms)		Vss	40	V
	non repetitive t=0.1ms	lo	4.5	А
Output Peak Current (Note)	repetitive f ≥10Hz	lo	3.5	Α
Power Dissipation at Tc=60℃	Power Dissipation at Tc=60°C		30	W
Junction Temperature		Τυ	+150	$^{\circ}$ C
Storage Temperature	T _{STG}	-40 ~ 150	°C	

Note: The max. output current is internally limited.

THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Thermal Resistance Junction-Case	θις	3.0	°C/W



ELECTRICAL CHARACTERISTICS

(Refer to the application circuit, Ta=25°C, Gv=50dB, Rth(heatsink)=4°C/W, unless otherwise specified.)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
		BRIDGE				
Supply Voltage	Vss		8		18	V
Output Offset Voltage (between pin 8 and pin 10)	Vos	Vss=14.4V Vss=13.2V			150 150	mV mV
Total Quiescent Drain Current	ID	Vss=14.4V, R _L =4Ω Vss=13.2V, R _L =3.2Ω		75 70	150 160	mA mA
Output Power	Роит	THD=10%, f=1Hz Vss=14.4V, R_L =4 Ω R _L =3.2 Ω Vss=13.2V, R_L =3.2 Ω	18 20 17	20 22 19		W
Total Harmonic Distortion f=1KHz	THD	Vss=14.4V, R _L =4 Ω P _{OUT} =50mW ~ 15W			1	%
Total Harmonic Distortion 1–1KHZ	THU	Vss=13.2V, R_L =3.2 Ω P_{OUT} =50mW ~ 13W			1	%
Input Sensitivity f=1kHz	V_{IN}	P_{OUT} =2W, R_L =4 Ω P_{OUT} =2W, R_L =3.2 Ω		9		mV mV
Input Resistance	R _{IN}	f=1kHz	70			kΩ
Low Frequency Roll Off (-3dB)	fL	R _L =3.2Ω			40	Hz
High Frequency Roll Off (-3dB)	f _H	R _L =3.2Ω	20			kHz
Closed Loop Voltage Gain	Gv	f=1kHz		50		dB
Total Input Noise Voltage	eN	R _G =10kΩ(Note 1)		3	10	μV
Supply Voltage Rejection	SVR	R_G =10k Ω , C4=10 μ F F_{RIPPLE} =100Hz, V_{RIPPLE} =0.5V	45	55		dB
Efficiency	η	Vss=14.4V, f=1kHz $P_{OUT}=20W, R_{L}=4\Omega$ $P_{OUT}=22W, R_{L}=3.2\Omega$ Vss=13.2V, f=1kHz $P_{OUT}=19W, R_{L}=3.2\Omega$		60 60 58		%
Thermal Shut-down Junction Temperature	TJ	Vss=14.4V, R_L =4 Ω f=1kHz, P_D =13W		145		°C
Output Voltage With One Side of the Speaker Shorted to Ground	Vosh	Vss=14.4V, R _L =4Ω Vss=13.2V, R _L =3.2Ω			2	V
		STEREO				
Supply Voltage	Vss		8		18	V
Quiescent Output Voltage	Vоит	Vss=14.4V Vss=13.2V	6.6 6	7.2 6.6	7.8 7.2	V



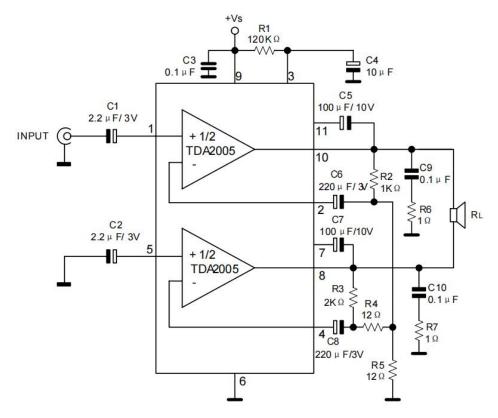
Total Quiescent Drain Current	I _D	Vss=14.4V			65	120	mA
		Vss=13.2V			62	120	mA
			R _L =4Ω	6	6.5		_
		Vss=14.4V	R _L =3.2Ω	7	8		
Output Power (each channel)			R _L =2Ω	9	10		
f=1Hz, THD=10%	Роит		R _L =1.6Ω	10	11		W
		Vss=13.2V	R _L =3.2Ω	6	6.5		
			R _L =1.6Ω	9	10		
		Vss=16V, R _L =2Ω			12		
		Vss=14.4V, R _L =49	Ω		0.0	4	0/
		P _{OUT} =50mW ~ 4V	V		0.2	1	%
		Vss=14.4V, RL=2	Ω		0.2	1	%
Total Harmonic Distortion (each	THD	Р _{ОUТ} =50mW ~ 6V	V		0.3	1	70
channel) f=1KHz		Vss=13.2V, R _L =3.	.2Ω		0.2	1	%
		POUT=50mW ~ 3	3W		0.2	'	70
		Vss=13.2V, R _L =1.	.6Ω		0.3	1	%
		P _{OUT} =40mW ~ 6V	V		0.5	'	/0
		Vss=14.4V,	f=1KHz		60		
Cross Talk	Ст	V _{OUT} =4VRMS	f=10kHz				dB
		$R_L=4\Omega$,	I-TOKI IZ		45		"-
		R _G =5KΩ					
Input Saturation Voltage	V _{IN}			300			mV
					_		l
Input Sensitivity	VIN	f=1kHz, P _{OUT} =1W R _L =4Ω			6		mV
Innut Decistance	RIN	RL=3.2Ω f=1kHz		70	5.5		1,0
Input Resistance Low Frequency Roll Off (-3dB)	fL	R _L =2Ω		70	200	50	kΩ
High Frequency Roll Off (-3dB)	fH	$R_L=2\Omega$		15		50	Hz kHz
Voltage Gain (open loop)	GV	f=1kHz		13	90		dB
Voltage Gain (close loop)	GV	f=1kHz		48	50	51	dB
Closed Loop Gain Matching	∆GV	I- IKIIZ		40	0.5	31	dB
Total Input Noise Voltage	En	R _G =10kΩ (Note 1)		1.5	5	μV
Supply Voltage Rejection	SVR	` ′			1.5		μV
Cappiy Voltage (Vojection	OVIC	· ·	R_G =10kΩ, C3=10μF F_{RIPPLE} =100Hz, V_{RIPPLE} =0.5V				dB
		Vss=14.4V, f=1kH					
		P _{OUT} =6.5W, R _L =4		70		%	
Efficiency	η	P _{OUT} =10W, R _L =20		60		%	
		Vss=13.2V, f=1kH					
		P _{OUT} =6.5W, R _L =3		70		%	
		P _{OUT} =100W, R _L =1	1.6Ω		60		%

Note: 1. Bandwith Filter: 22Hz ~ 22kHz

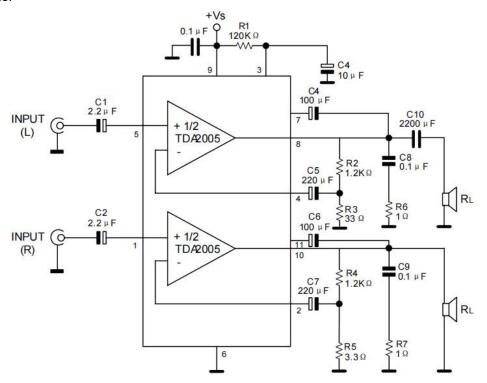


TEST AND APPLICATION CIRCUIT

Bridge amplifier



Stereo amplifier





BRIDGE AMPLIFIER DESIGN

The following consideraions can be useful when designing a bridge amplifier.

	PARAMETER	SINGLE ENDED	BRIDGE
V _{OUT} max	Peak Output Voltage (before clipping)	$\frac{1}{2}$ (Vs-2V _{CE} sat)	Vs-2V _{CE} sat
I _{OUT} max	Peak Output Current (before clipping)	$\frac{1}{2} \frac{V_{S-2}V_{CE} \text{ sat}}{R_L}$	$\frac{\text{Vs} - 2\text{V}_{\text{CE}} \text{ sat}}{\text{R}_{\text{L}}}$
P _{OUT} max	RMS Output Power (before clipping)	$\frac{1}{4} \frac{(Vs - 2V_{CE} \text{ sat})^2}{2R_L}$	$\frac{(\text{Vs} - 2\text{V}_{\text{CE}} \text{ sat})^2}{2\text{R}_{\text{L}}}$

Where: V_{CE} sat=output transistors saturation voltage

Vs=allowable supply voltage

R_L=load impedance

Voltage and current swings are twice for a bridge amplifier in comparison with single ended amplifier. In order words, with the same RL the bridge configuration can deliver an output power that is four times the output power of a single ended amplifier, while, with the same max output current the bridge configuration can deliver an output power that is twice the output power of a single ended amplifier. Core must be taken when selecting Vs and RL in order to avoid an output peak current above the absolute maximum rating.

From the expression for Io max, assuming Vs=14.4V and VCE sat=2V, the minimum load that can be driven by TDA2005 in bridge configuration is:

RL min=
$$\frac{\text{Vs-2VcEsat}}{\text{lout max}} = \frac{14.4 - 4}{3.5} = 2.97 \,\Omega$$

The voltage gain of the bridge configuration is given by (see Figure 3):

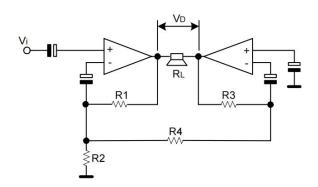
$$GV = \frac{V_0}{V_1} = 1 + \frac{R_1}{\left(\frac{R_2 \times R_4}{R_2 + R_4}\right)} + \frac{R_3}{R_4}$$

For sufficiently high gains (40 ~ 50dB) it is possible to put R2=R4 and R3=2R1, simplifing the formula in:

$$Gv=4\frac{R_1}{R_2}$$

Gv (dB)	R1(Ω)	R2=R4(Ω)	R3(Ω)
40	1000	39	2000
50	1000	12	2000

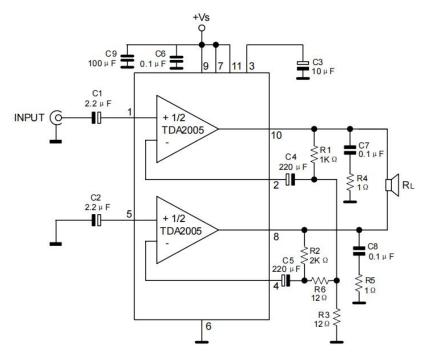
Bridge Configuratio



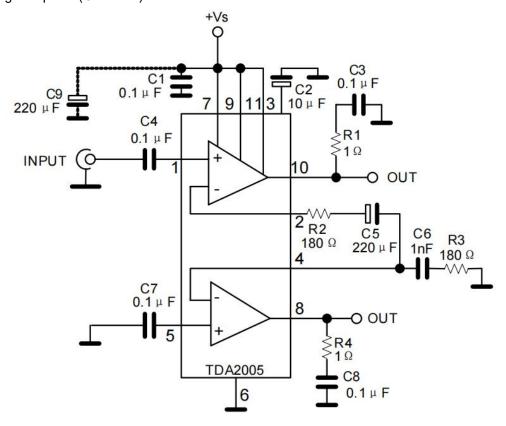


APPLICATION INFORMATION

Bridge Amplifier without Boostrap



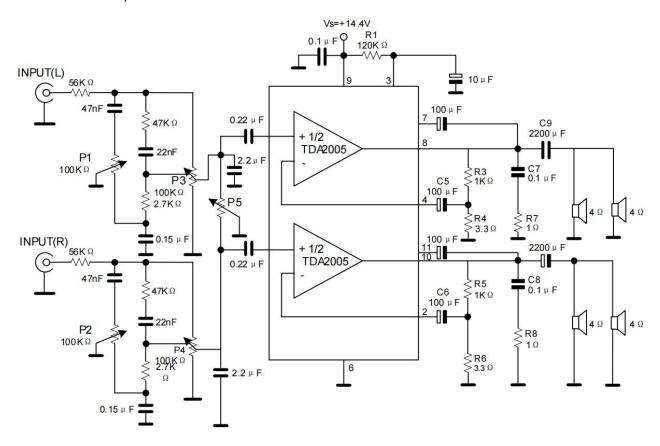
Low Cost Bridge Amplifier (Gv=42dB)



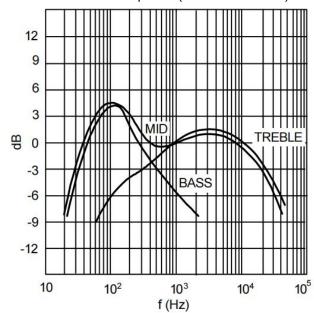


APPLICATION INFORMATION(Cont.)

10+10W Stereo Amplifier with Tone Balance and Loudness Control



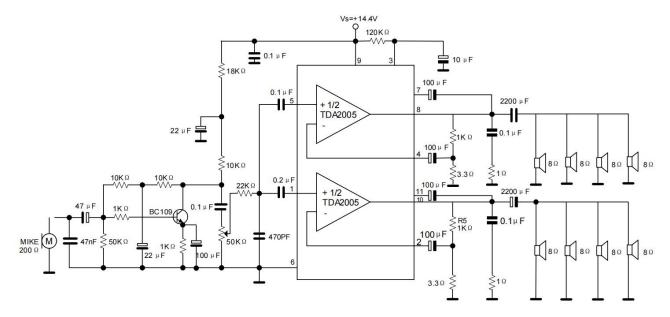
Tone Control Response (circuit of Fihure 8)



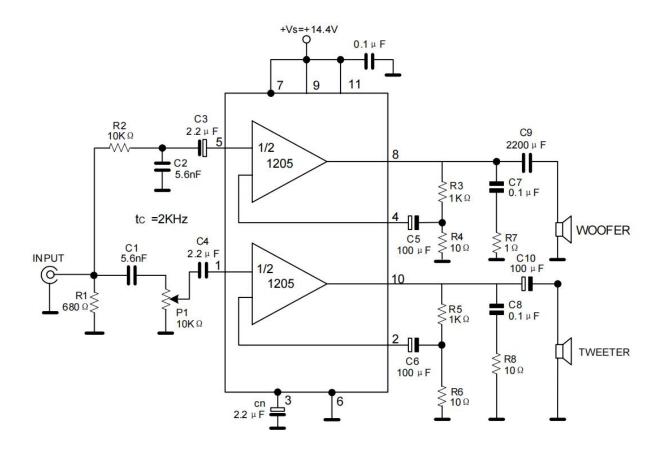


APPLICATION INFORMATION(Cont.)

20W Bus Amplifier



Simple 20W Two Way Amplifier (Fc=2kHz)





APPLICATION INFORMATION(Cont.)

Bridge Amplifier Circuit suited for Low-gain Applications (Gv=34dB)

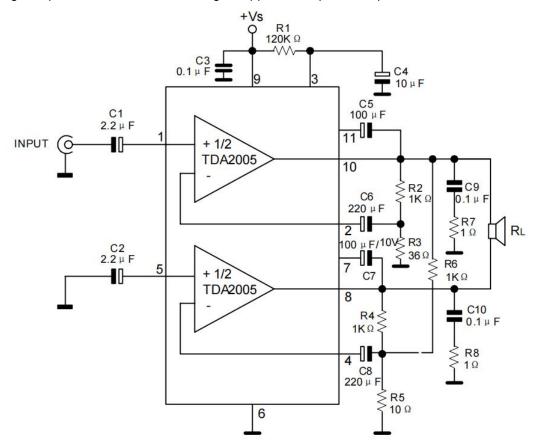
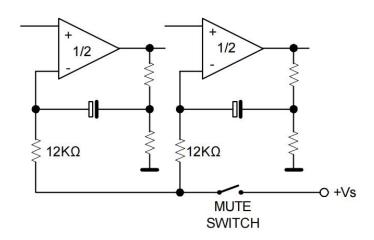


Figure 1. Example of Muting Circuit





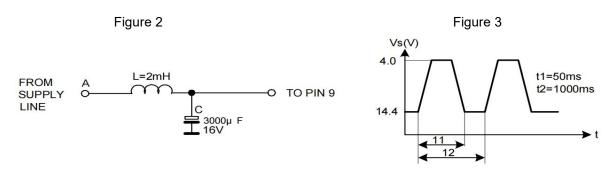
BUILT-IN PROTECTION SYSTEMS

LOAD DUMP VOLTAGE SURGE

The TDA2005 has a circuit which enables it to withstand a voltage pulse train, on pin9, of the type shown in Figure 3.

If the supply voltage peaks to more than 40V, then an LC filter must be inserted between the supply and pin9, in order to assure that the pulses at pin 9 will be held withing the limits shown.

A suggested LC network is shown in Figure 2, With this network, a train of pulses with amplitude up to 120V and width of 2ms can be applied at point A, This type of protection is ON when the supply voltage (pulse or DC) exceeds 18V. For this reason the maximum operating supply voltage is 18V.



SHORT CIRCUIT (AC AND DC CONDITIONS)

The TDA2005 can withstand a permanent short circuit on the output for a supply voltage up to 16V.

POLARITY INVERSION

High current (up to 10A) can be handled by the device with no damage for a longer period than the blow-out time of a quick 2A fuse (normally connected in series with the supply). This feature is added to avoid destruction, if during fitting to the car, a mistake on the connection of the supply is made.

OPEN GROUND

When the ratio is in the ON condition and the ground is accidentally opened, a standard audio amplifier will be damaged. On the TDA2005 protection diodes are included to avoid any damage.

INDUCTIVE LOAD

A protection diode is provided to allow use of the TDA2005 with inductive loads.

DC VOLTAGE

The maxim operating DC voltage for the TDA2005 is 18V.

However the device can withstand a DC voltage up to 28V with no damage. This could occur during winter if two batteries are series connected to crank the engine.

THERMAL SHUT-DOWN

The presence of a thermal limiting circuit offers the following advantages:

- (1). An overload on the output (even if it is permanent), or an excessive ambient temperature can be easily withstood.
- (2). The heatsink can have a smaller factor of safety compared with that of a conventional circuit. There is no device damage in the case of excessive junction temperature; all that happens is that Po (and therefore Ptot) and Id are reduced.

The maximum allowable power dissipation depends upon the size of the external heatsink (i.e. its thermal resistance); Figure 4 shows the dissipation power as a function of ambient temperature for different thermal resistance.

LOUDSPEAKER PROTECTION

The circuit offers loudspeaker protection during short circuit for one wire to ground.



TYPICAL CHARACTORISTICS

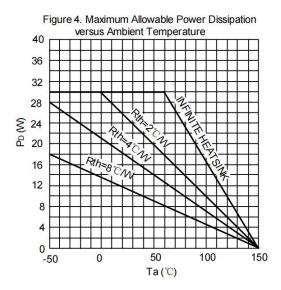


Figure 6. Output Power and Drain Current Versus
Case Temperature

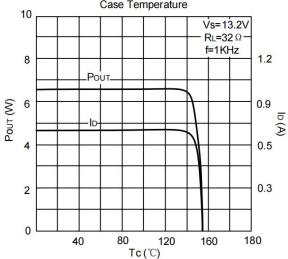


Figure 8. Distortion versus Output Power (bridge amplifier)

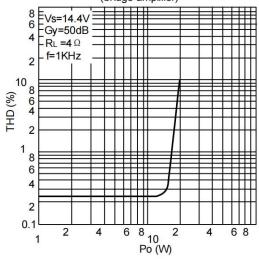


Figure 5. Output Power and Drain Current Versus

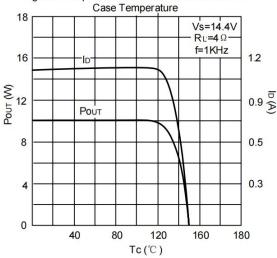


Figure 7. Output Offset Voltage versus Supply Voltage

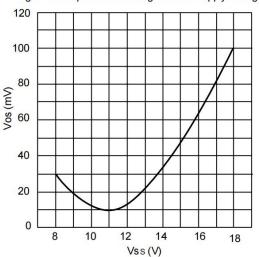
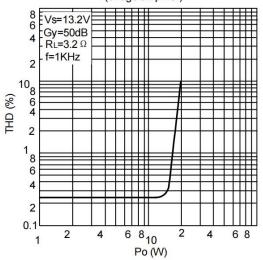
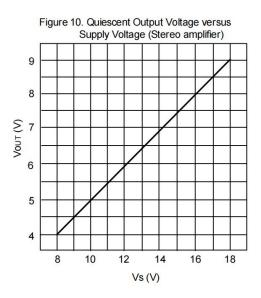


Figure 9. Distortion versus Output Power (bridge amplifier)





TYPICAL CHARACTORISTICS (cont.)



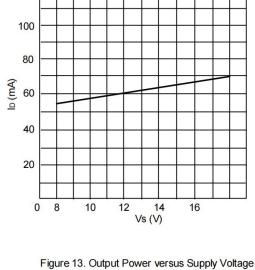
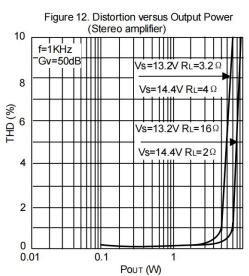
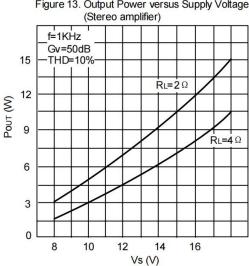
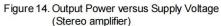


Figure 11. Quiescent Drain Current versus

Supply Voltage(Stereo amplifier)







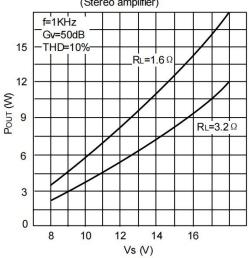
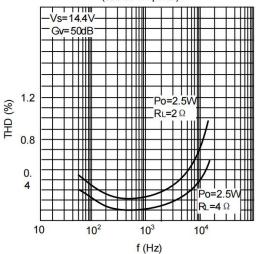
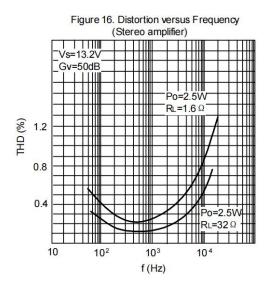


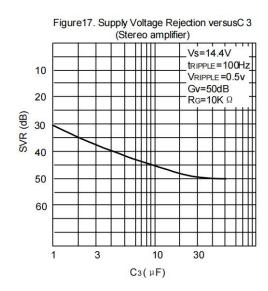
Figure 15. Distortion versus Frequency (Stereo amplifier)





TYPICAL CHARACTORISTICS (cont.)





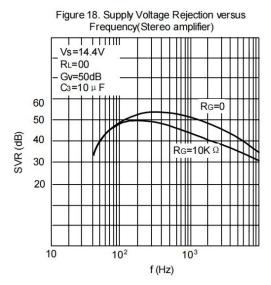
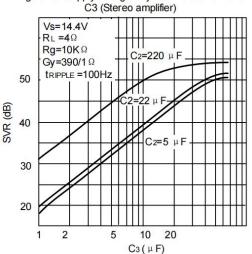
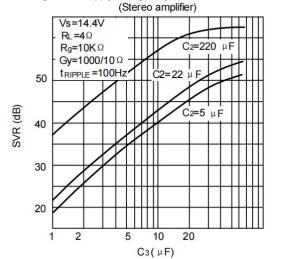


Figure 20. Supply Voltage Rejection versus C 2 and C3





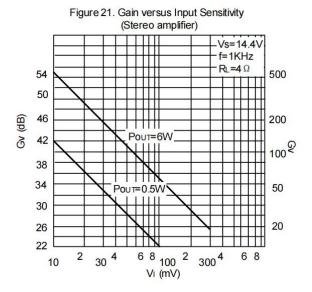


Figure 19. Supply Voltage Rejection versus C 2 and C3 (Stereo amplifier)



TYPICAL CHARACTORISTICS (cont.)

Figure 22. Gain versus Input Sensitivity (Stereo amplifier)

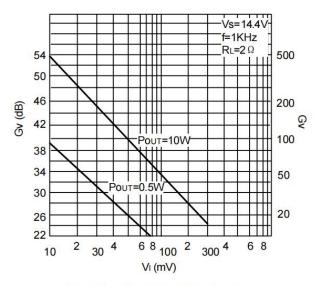


Figure 24. Total Power Dissipation and Efficiency versus Output Power (Stereo amplifier)

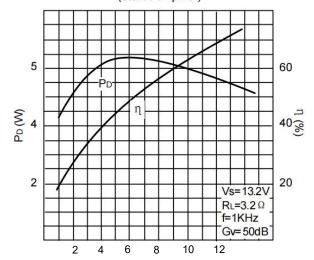
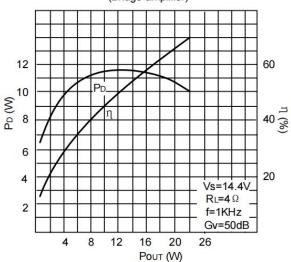


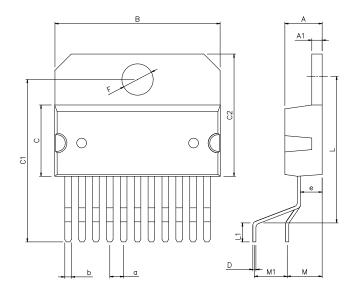
Figure 23. Total Power Dissipation and Efficiency versus Output Power (Bridge amplifier)





Physical Dimensions

ZIP-11



Dimensions In Millimeters(ZIP-11)															
Symbol:	Α	A1	В	С	C1	C2	D	F	L	L1	М	M1	а	b	е
Min:	4.4	1.2	19.6	10.3	21.9	17.2	0.49	3.65	17.4	3.2	4.25	4.73	1.45	0.88	2.65
Max:	5.0	1.6	20.6	10.9	22.5	17.7	0.55	3.85	18.1	4.5	4.85	5.43	1.95	0.95	TYP



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